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IN THE CLAIMS:

The following listing of claims replaces all prior versions and listings of claims in the present application:

Listing of Claims:

1. (Currently amended) A method for manufacturing a compound semiconductor epitaxial substrate comprising a step of epitaxially growing an InGaAs layer on an InP single crystal substrate or on an epitaxial layer lattice-matched to the InP single crystal substrate under conditions of

ratio of V/III: 10 - 100,

growth temperature: 630°C - 700°C, and

growth rate: 0.6 μm/h - 2 μm/h,

wherein the InP single crystal substrate has a plane direction accuracy of ±0.05° in the (100).

2. (Cancelled)

3. (Previously presented) The method according to claim 1, wherein the epitaxially growing is carried out by using metal-organic chemical vapor deposition (MOCVD).

4. (Previously presented). The method according to claim 1, wherein the epitaxially growing of the InGaAs layer includes use of

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gallium raw material selected from the group consisting of trimethyl gallium and triethyl gallium.

5. (*Previously presented*) The method according to claim 1, wherein the epitaxial growing of the InGaAs layer includes use of indium raw material comprising trimethyl indium.

6. (*Currently amended*) The method according to claim 1, wherein the epitaxial growing of the InGaAs layer includes use of arsenic raw material comprising arsine.

7. (*Original*) A method for reducing concave defects in a compound semiconductor epitaxial substrate comprising a step of epitaxially growing an InGaAs layer on an InP single crystal substrate or on an epitaxial layer lattice-matched to the InP single-crystal substrate under conditions of ratio of V/III: 10 to 100, growth temperature: 630°C - 700°C, and growth rate: 0.6 μm/h - 2 μm/h,
wherein the InP single crystal substrate has a plane direction accuracy of ±0.05° in the (100).

8. (*Currently amended*) A compound semiconductor epitaxial substrate obtained by using the method according to claim 1.